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Rhombohedral Hf_{0.5}Zr_{0.5}O₂ thin films

Wei, Yingfen

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Rhombohedral Hf_{0.5}Zr_{0.5}O₂ thin films
Ferroelectricity and Devices

Yingfen Wei



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Rhombohedral $\text{Hf}_{0.5}\text{Zr}_{0.5}\text{O}_2$ thin films

Ferroelectricity and Devices

PhD thesis

to obtain the degree of PhD at the
University of Groningen
on the authority of the
Rector Magnificus prof. dr. E. Sterken,
and in accordance with
the decision by the College of Deans.

This thesis will be defended in public on

Friday 17 January 2020 at 16:15 hours

by

Yingfen Wei

born on 6 June 1990
in Jiangsu, China

Promotors

Prof. B. Noheda

Prof. B. J. Kooi

Assessment Committee

Prof. B. J. van Wees

Prof. G. Koster

Prof. J. Santamaria

To my family, friends and teachers

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